

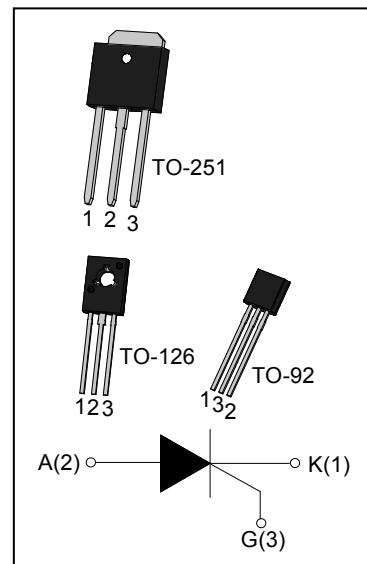


## JX020 Series Sensitive gate SCRs

Rev.11.0

## DESCRIPTION:

The JX020 SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc. All of the three packages listed above are RoHS compliant. (2011/65/EU)



## MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
$I_{GT}$	$\leq 200$	$\mu A$

## ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125 <sup>①</sup>	°C
Repetitive peak off-state voltage	$V_{DRM}$	600	V
Repetitive peak reverse voltage	$V_{RRM}$	600	V
RMS on-state current	$I_{T(RMS)}$	2	A
Non repetitive surge peak on-state current (F=50Hz tp=10ms)	$I_{TSM}$	20	A
Non repetitive surge peak on-state current (F=60Hz tp=8.3ms)	$I_{TSM}$	22	A
$I^2t$ value for fusing (tp=10ms)	$I^2t$	2	$A^2s$
Critical rate of rise of on-state current	$dI/dt$	50	$A/\mu s$
Peak gate current (tp=20μs, $T_j=125^\circ C$ )	$I_{GM}$	0.2	A
Peak gate power (tp=20μs, $T_j=125^\circ C$ )	$P_{GM}$	0.5	W
Average gate power dissipation( $T_j=125^\circ C$ )	$P_{G(AV)}$	0.1	W

**NOTE 1:** When we parallel connect a  $\leq 1K\Omega$  resistor between Gate and Cathode, the  $T_j$  can reach  $125^\circ C$ ; if without this resistor, the  $T_j$  only can reach  $110^\circ C$ .

ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V R_L=33\Omega$	-	50	200	$\mu\text{A}$
$V_{GT}$		-	0.6	0.8	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$	0.2	-	-	V
$I_L$	$I_G=1.2 I_{GT}$	-	-	6	mA
$I_H$	$I_T=0.05\text{A}$	-	-	5	mA
$dV/dt$	$V_D=400V T_j=125^\circ\text{C} R_{GK}=1\text{K}\Omega$	60	-	-	V/ $\mu\text{s}$
	$V_D=400V T_j=125^\circ\text{C} R_{GK}=220\Omega$	500	-	-	
$R_d$	Dynamic Resistance $T_j=125^\circ\text{C}$	-	-	180	$\text{m}\Omega$

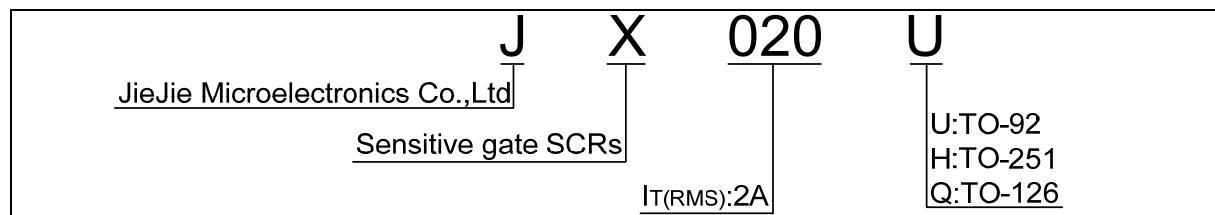
## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_T=4\text{A} t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	100	$\mu\text{A}$

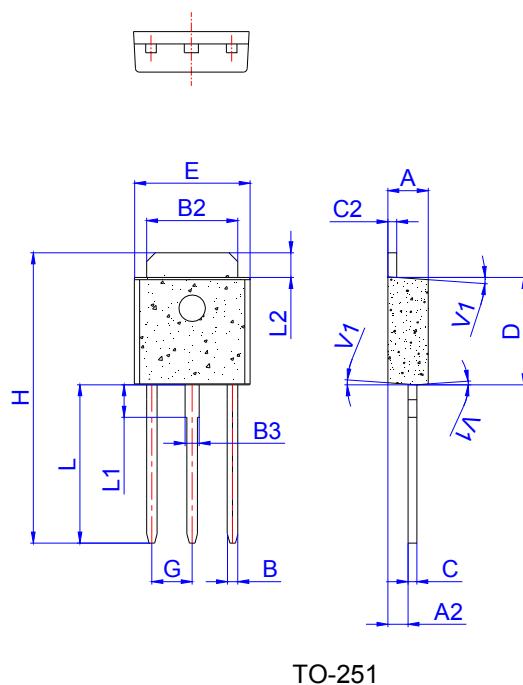
## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case	TO-92	10	$^\circ\text{C}/\text{W}$
		TO-126	7.0	
		TO-251	6.5	

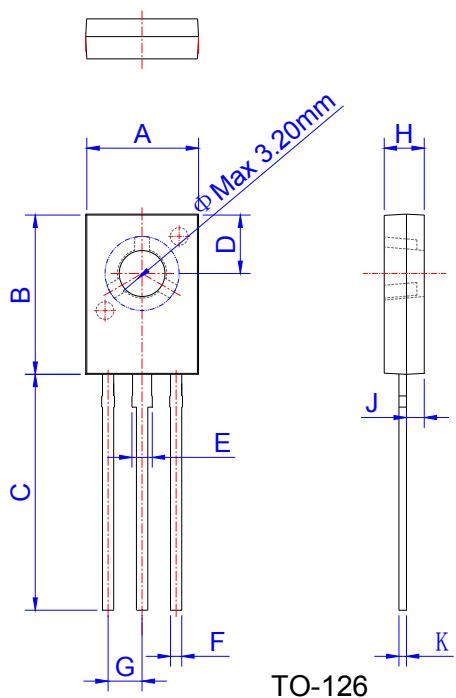
## ORDERING INFORMATION



## PACKAGE MECHANICAL DATA

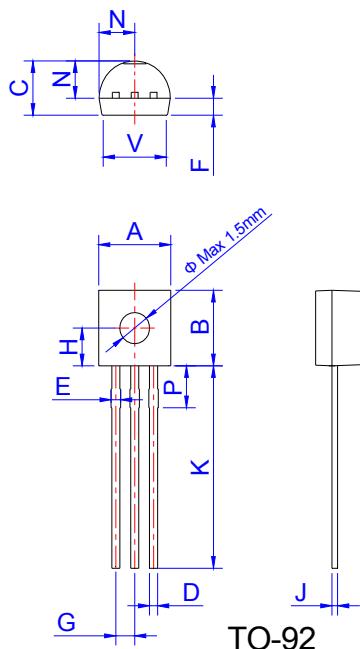


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

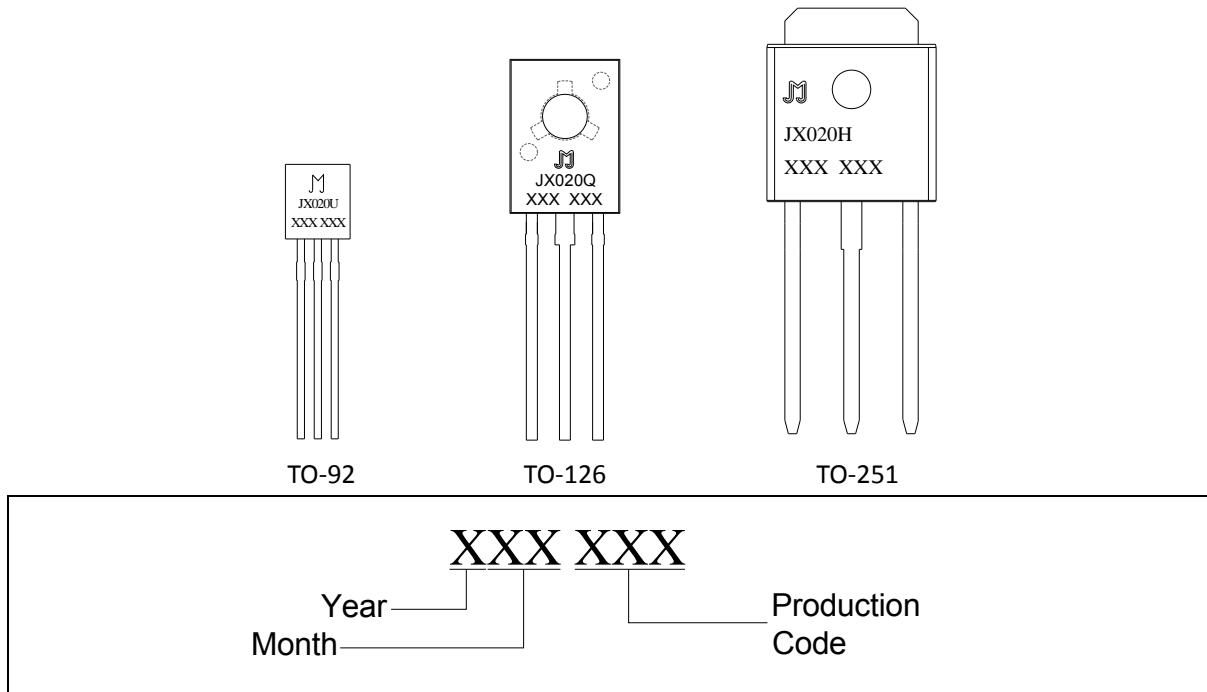
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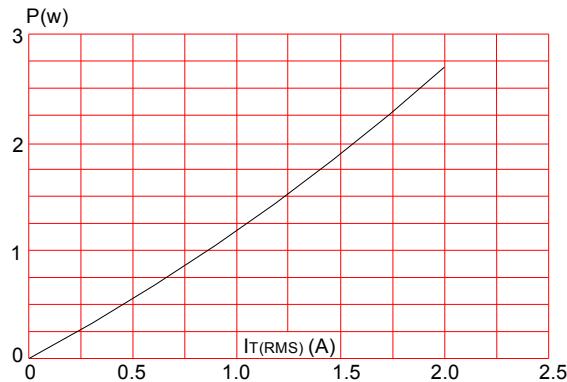
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.45		5.20	0.175		0.205
B	4.32		5.33	0.170		0.210
C	3.18		4.19	0.125		0.165
D	0.407		0.533	0.016		0.021
E	0.50		0.70	0.020		0.028
F	-	1.1	-	-	0.043	-
G	-	1.27	-	-	0.050	-
H	-	2.30	-	-	0.091	-
J	0.36		0.50	0.014		0.020
K	12.70		15.0	0.500		0.591
N	2.04		2.66	0.080		0.105
P	1.86		2.06	0.073		0.081
V	-		4.3	-		0.169

## PACKAGE INFORMATION

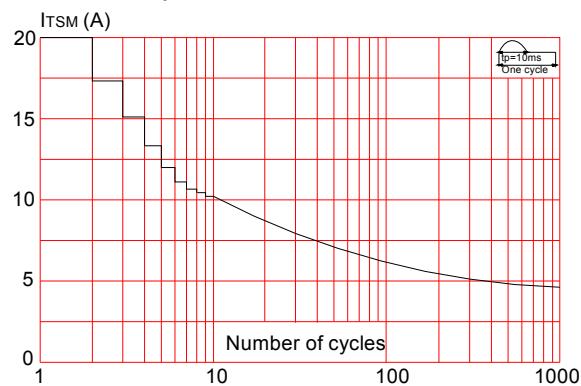
PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-126	TUBE	50	3,000	18,000
TO-251	TUBE	80	4,000	32,000
PACKAGE	OUTLINE	BAG (PCS)	INNER BOX (PCS)	PER CARTON
TO-92	Shielding Bag	1,000	10,000	50,000

**MARKING**

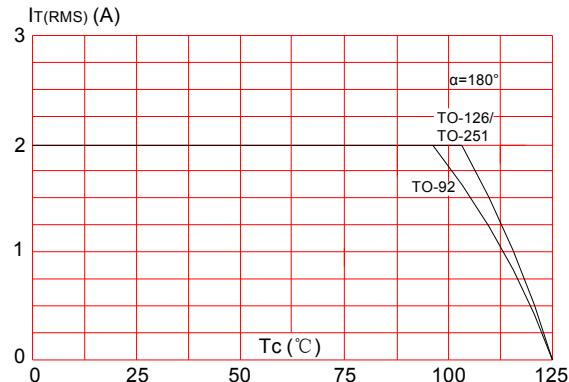
**FIG.1:** Maximum power dissipation versus RMS on-state current



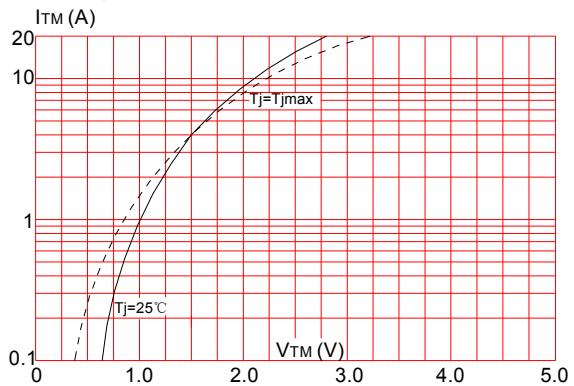
**FIG.3:** Surge peak on-state current versus number of cycles



**FIG.2:** RMS on-state current versus case temperature

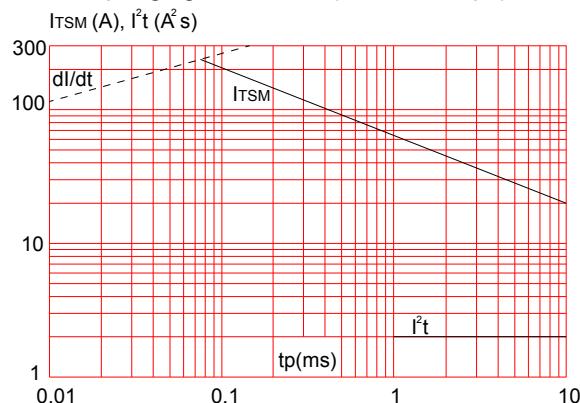


**FIG.4:** On-state characteristics (maximum values)

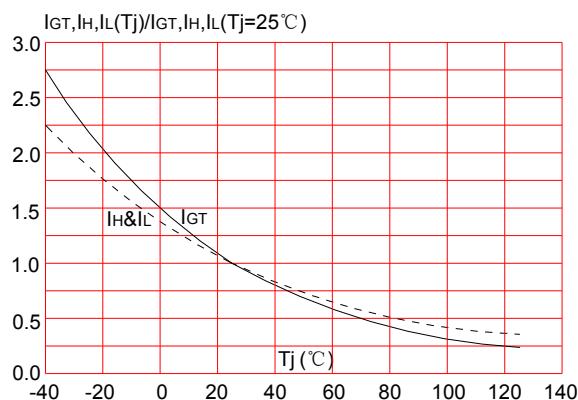




**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 50\text{A}/\mu\text{s}$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



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